

isc N-Channel MOSFET Transistor

2SK753

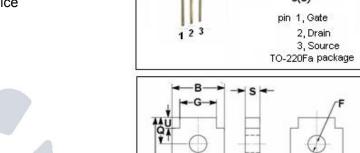
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DESCRIPTION

- Drain Current –I_D=5A@ T_C=25 °C
- · Drain Source Voltage-
- : V_{DSS}= 160V(Min)
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

· High speed power switching



ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	ARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage (V _{GS} =0)	160	٧
V _G s	Gate-Source Voltage	±20	V
ID	Drain Current-continuous@ TC=25℃	5	А
P _{tot}	Total Dissipation@TC=25℃	40	W
Tj	Max. Operating Junction Temperature	150	$^{\circ}$
T _{stg}	Storage Temperature Range	-55~150	$^{\circ}$

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H H K				I I I
<u> </u>		→ R	- J	
			J 1	STATE OF THE PARTY
		-dCa		∢N ►
	DIM	⊸C		STATE OF THE PARTY
	DIM A	⊸C: m	MAX 17.15	STATE OF THE PARTY
		MIN 16.85 9.54	m MAX	STATE OF THE PARTY
	A B C	MIN 16.85 9.54 4.35	MAX 17.15 10.10 4.65	STATE OF THE PARTY
	A B C D	MIN 16.85 9.54 4.35 0.75	MAX 17.15 10.10 4.65 0.90	STATE OF THE PARTY
	A B C D	MIN 16.85 9.54 4.35 0.75 3.20	MAX 17.15 10.10 4.65 0.90 3.40	STATE OF THE PARTY
	A B C D F	MIN 16.85 9.54 4.35 0.75 3.20 6.90	MAX 17.15 10.10 4.65 0.90 3.40 7.20	STATE OF THE PARTY
	A B C D F G	MIN 16.85 9.54 4.35 0.75 3.20 6.90 3.80	MAX 17.15 10.10 4.65 0.90 3.40 7.20 4.20	STATE OF THE PARTY
	A B C D F G H	MIN 16.85 9.54 4.35 0.75 3.20 6.90 3.80 0.45	MAX 17.15 10.10 4.65 0.90 3.40 7.20 4.20 0.75	STATE OF THE PARTY
	A B C D F G H J	MIN 16.85 9.54 4.35 0.75 3.20 6.90 3.80 0.45	MAX 17.15 10.10 4.65 0.90 3.40 7.20 4.20 0.75 13.80	STATE OF THE PARTY
	A B C D F G H J K	MIN 16.85 9.54 4.35 0.75 3.20 6.90 3.80 0.45 13.35	MAX 17.15 10.10 4.65 0.90 3.40 7.20 4.20 0.75 13.80	STATE OF THE PARTY
	A B C D F G H J	MIN 16.85 9.54 4.35 0.75 3.20 6.90 3.80 0.45	MAX 17.15 10.10 4.65 0.90 3.40 7.20 4.20 0.75 13.80	STATE OF THE PARTY
	A B C D F G H J K L	MIN 16.85 9.54 4.35 0.75 3.20 6.90 8.80 0.45 13.35 1.10 4.98 4.85	MAX 17.15 10.10 4.65 0.90 3.40 7.20 4.20 0.75 13.80 1.30	STATE OF THE PARTY
	A B C D F G H J K L N Q R	MIN 16.85 9.54 4.35 0.75 3.20 6.90 8.80 0.45 13.35 1.10 4.98 4.85 2.55	MAX 17.15 10.10 4.65 0.90 3.40 7.20 4.20 0.75 13.80 1.30 5.18	STATE OF THE PARTY
	A B C D F G H J K L N Q	MIN 16.85 9.54 4.35 0.75 3.20 6.90 8.80 0.45 13.35 1.10 4.98 4.85	MAX 17.15 10.10 4.65 0.90 3.40 7.20 4.20 0.75 13.80 1.30 5.18 5.15 3.25	STATE OF THE PARTY



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• ELECTRICAL CHARACTERISTICS (Tc=25°C)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 10mA	160			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =10 V _{GS} ; I _D =1mA	1.0		5.0	V
R _{DS(on)}	Drain-Source On-stage Resistance	V _{GS} =10V; I _D = 3A			0.5	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±16V;V _{DS} = 0			±10	uA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =120V; V _{GS} = 0			250	uA
V _{SD}	Diode Forward Voltage	I _F =5A; V _{GS} =0		1.0		V



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